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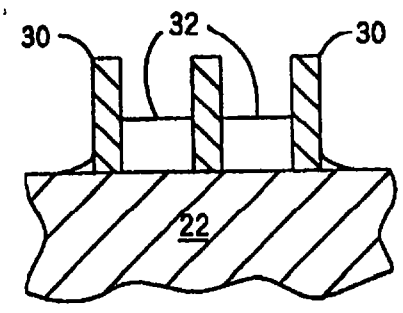
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(54) Title: METHOD AND EVAPORATING SOLUTION FOR RINSING A DEVELOPED PHOTORESIST LAYER

(57) Abstract: A method of developing a photoresist layer (30) on a semiconductor wafer (22) in a developing chamber (20) includes applying a developer to the photoresist layer (30), applying an evaporating solution (32) to the photoresist layer (30), and drying the wafer (22).



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